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(54) Title: ORGANIC THIN FILM TRANSISTOR

(57) Abstract: An organic thin film transistor utilizing an organic semiconductor film is composed of a first substrate, a gate electrode, a gate insulation film, an organic semiconductor film, a source electrode, a drain electrode, a protective film and a second substrate, and produced by forming a gate electrode, a gate insulation film, an organic semiconductor film, a source electrode, and a drain electrode on a first substrate, forming a protective film on a second substrate, and superposing a surface, bearing the organic semiconductor film, of the first substrate upon a surface, bearing the protective film, of the second substrate.